

FIG. 1

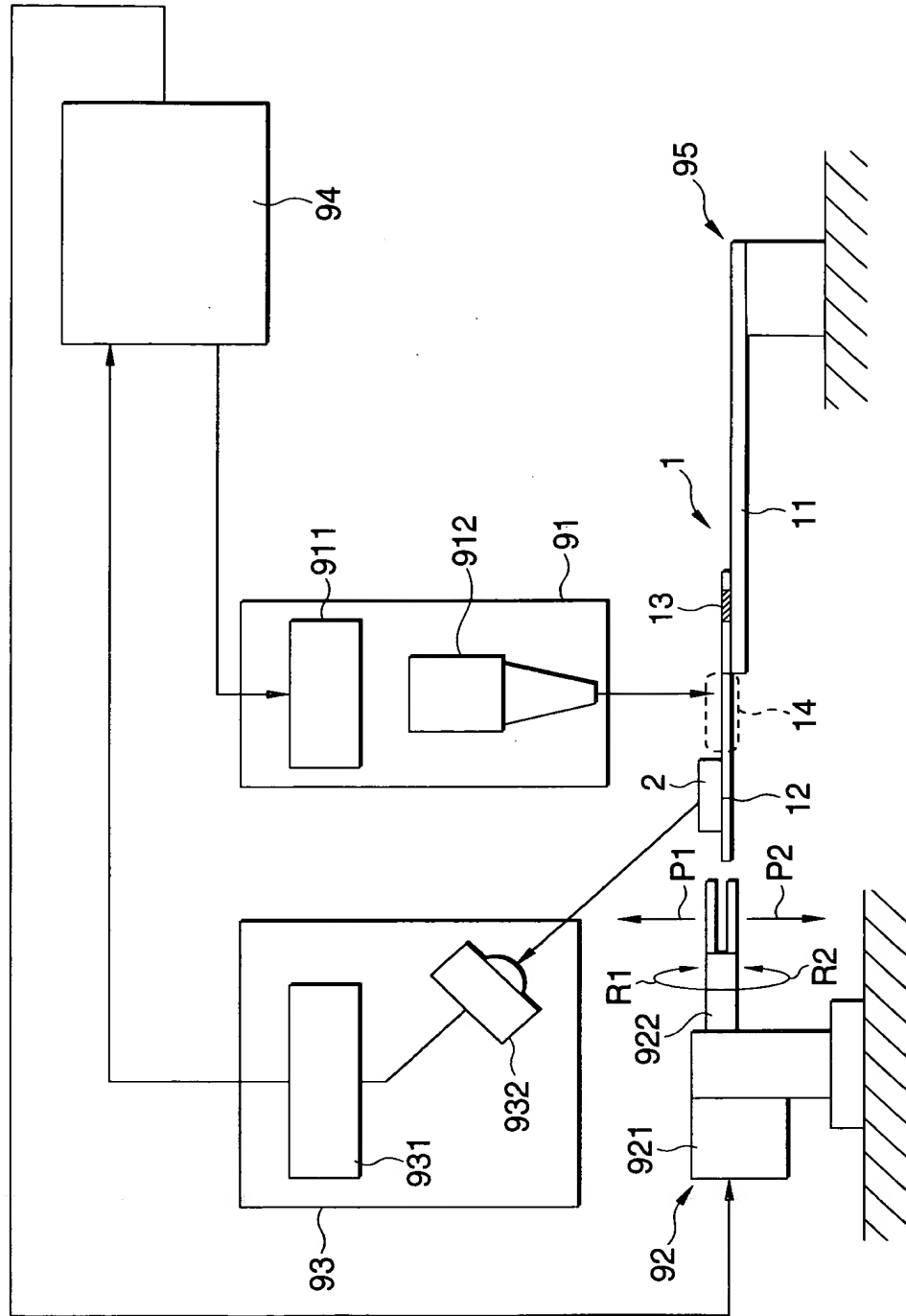


FIG. 2

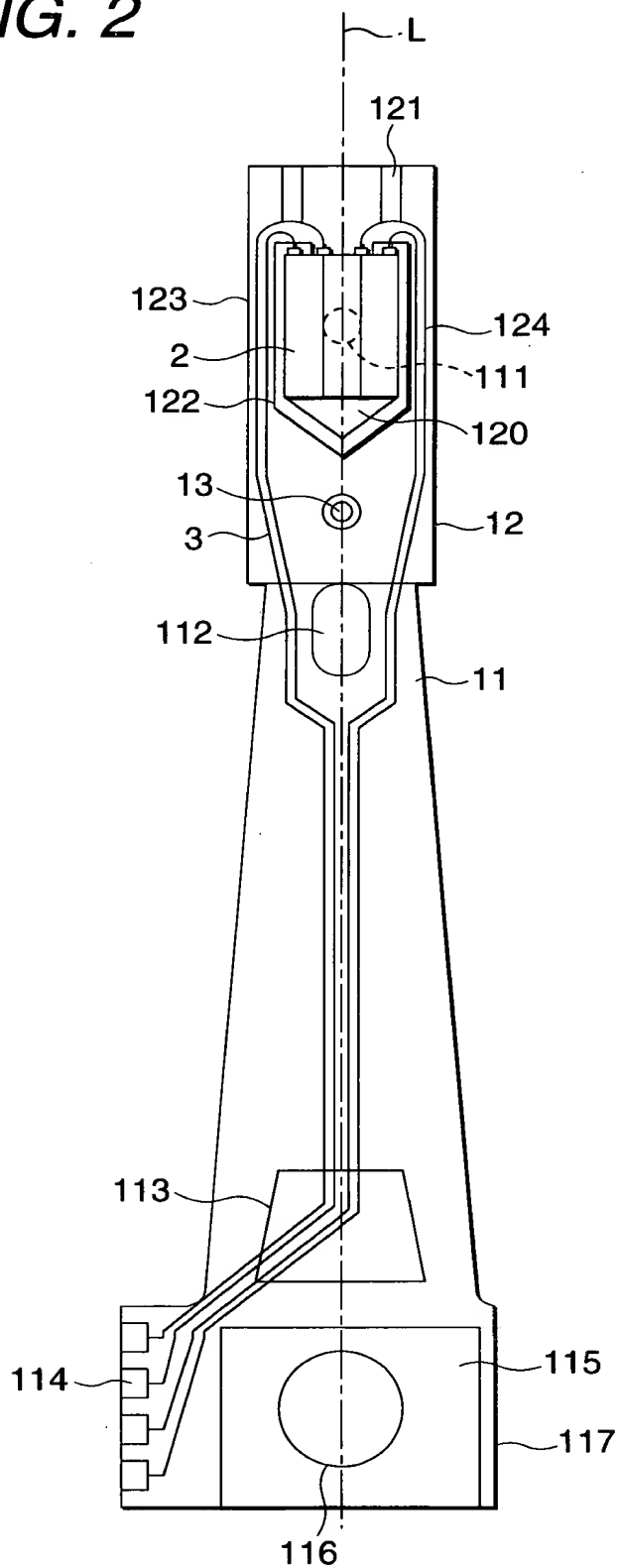


FIG. 3

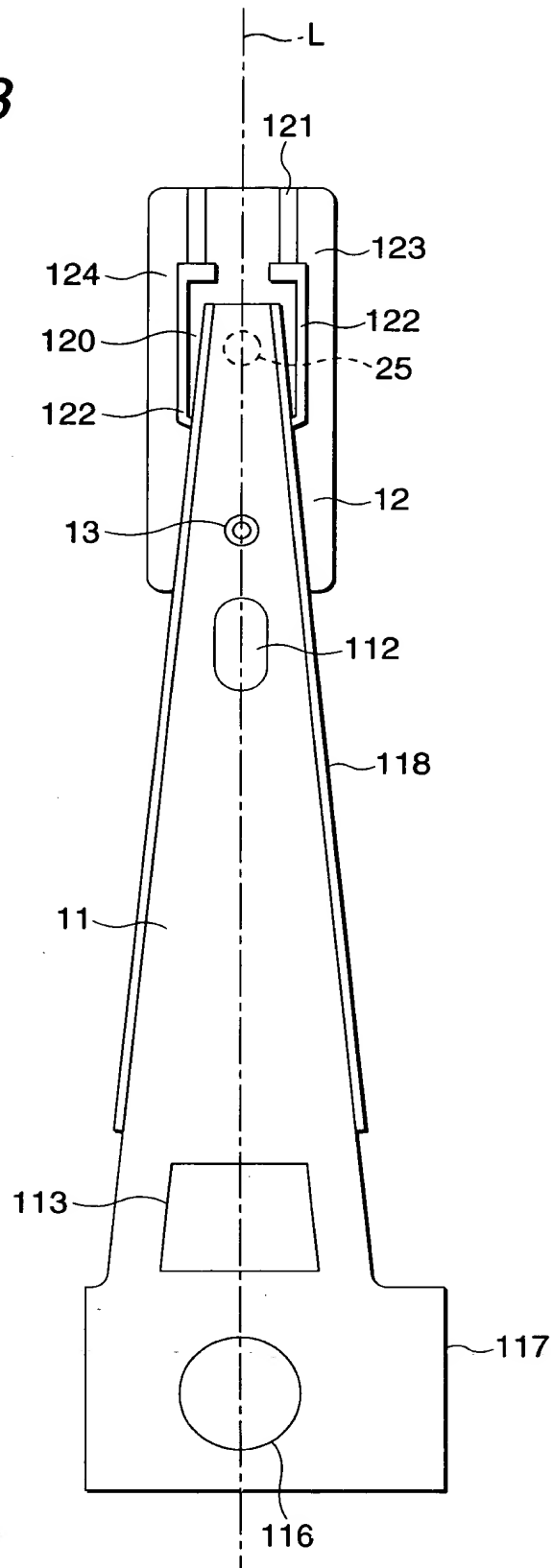


FIG. 4

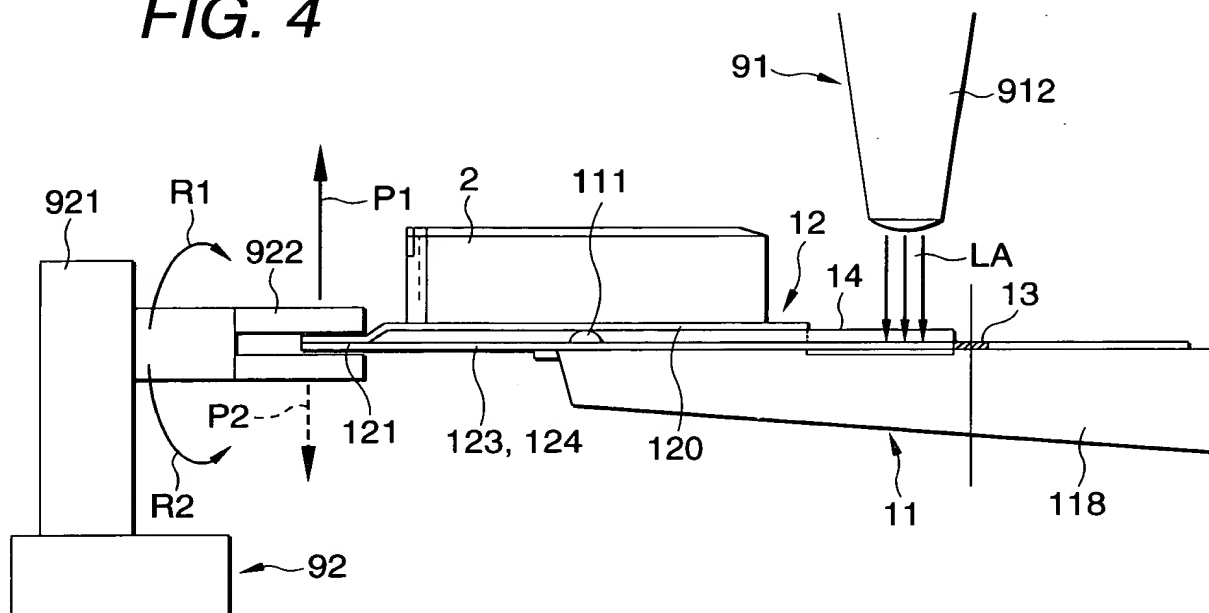
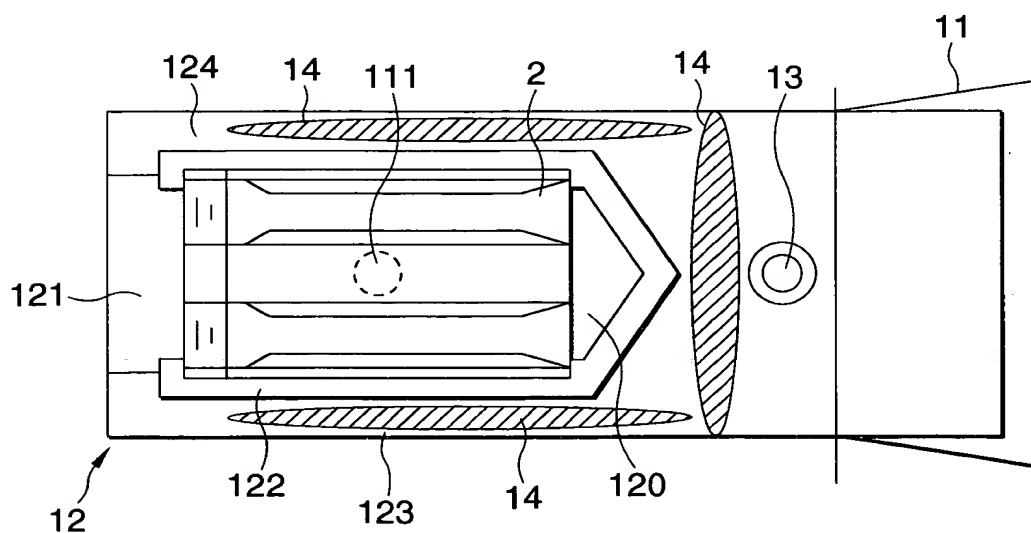


FIG. 5



[illegible]

A cross-sectional diagram of a semiconductor device assembly. A substrate 118 is shown at the bottom right, sloping upwards to the left. On top of the substrate is a layer 11. A vertical structure 91 is positioned above the substrate, with its tip labeled 912. The tip 912 is emitting three downward arrows labeled LA. To the left of the substrate, there is a larger rectangular component 92. Inside or on top of component 92 are several layers and structures: a layer 120, a layer 123, 124, a layer 121, and a layer 12. A curved arrow R1 indicates a rotation around a horizontal axis passing through the center of the assembly. Another curved arrow R2 indicates a rotation around a vertical axis passing through the center of the assembly. An upward arrow P1 points from the top surface of the assembly, and a dashed downward arrow P2 points from the bottom surface of the assembly. Other labels include 921, 922, 111, 12, 14, and 13.

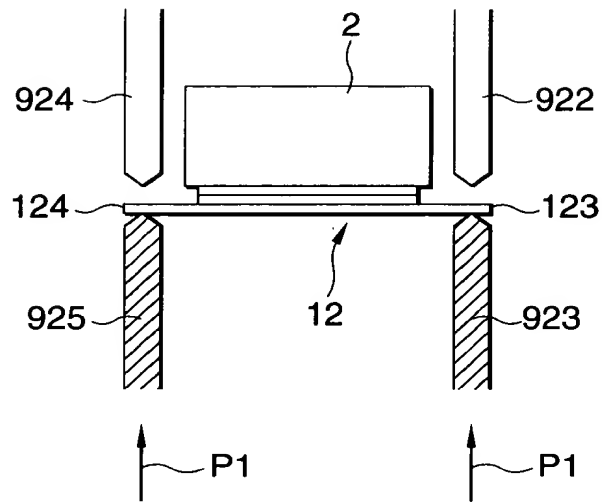
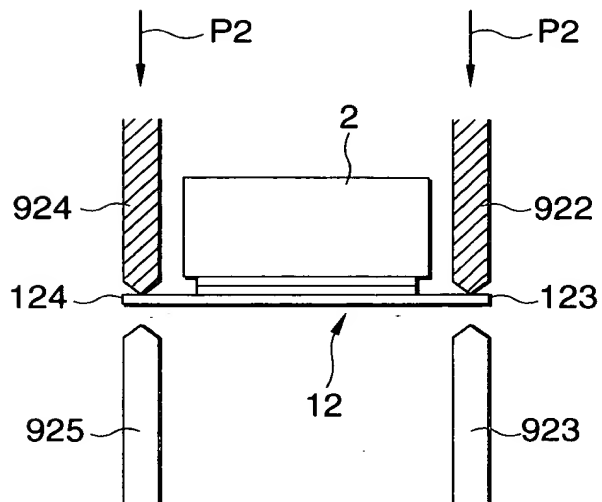
FIG. 10**FIG. 11**

FIG. 12

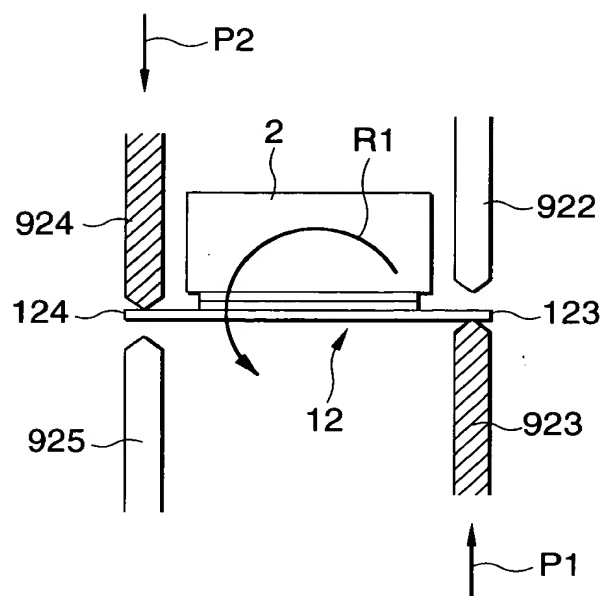


FIG. 13

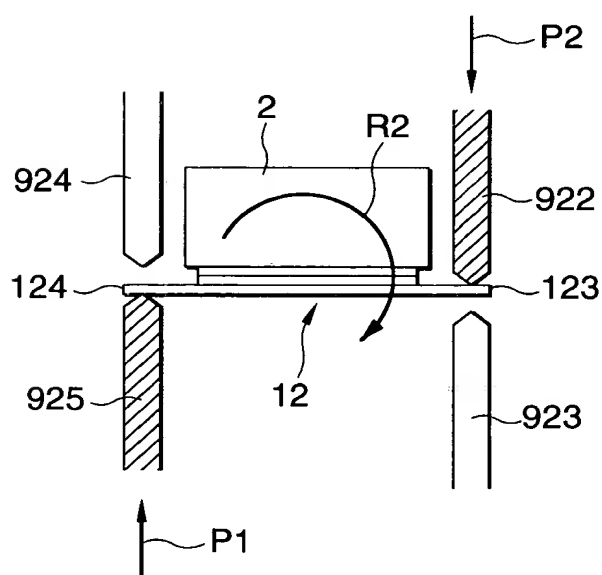


FIG. 14

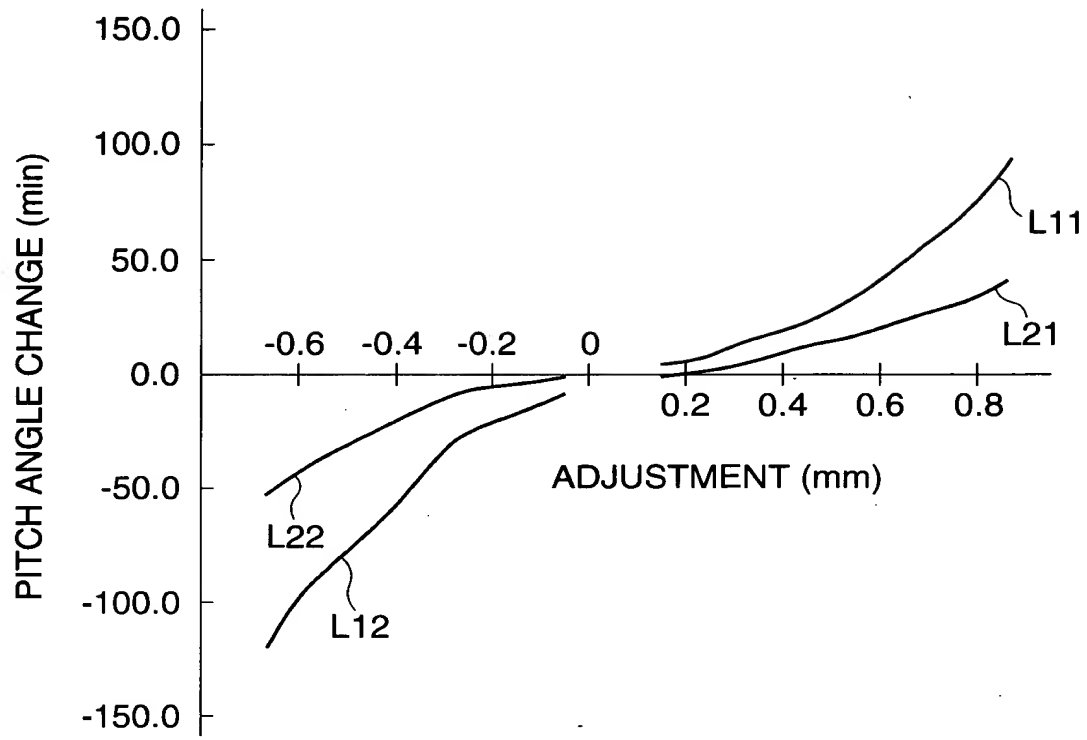


FIG. 15

